

CLAIMS

1. A method of removing an organic light-emitting material from defined areas of a substrate comprising the steps of arranging a shadow mask to overlie the organic material other than in the defined areas, and
5 applying a beam of ions to the defined areas through the mask.

2. A method according to claim 1, wherein the organic light-emitting material is polymeric.
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3. A method according to claim 1 or 2, wherein at least one of the mask and the substrate has recesses in its surface facing the other of the mask and the substrate.

15 4. A method according to claim 1, 2 or 3, wherein the ions are chemically reactive with the organic material to be etched.

5. A method according to any preceding claim, wherein the ions are ions of a normally inert gas.

20 6. A method according to claim 5, wherein the ions are Argon ions.

7. A method according to any preceding claim, wherein the step of applying the beam of ions is carried out in a chamber having dimensions, at
25 a pressure at which the mean free path of the ions is greater than or equivalent to the chamber dimensions.

8. A method according to any preceding claim, wherein the step of applying the beam of ions is carried out at a pressure less than 5×10^{-4} mbar.

9. A method according to any preceding claim, wherein the organic material is formed from an organic layer of an array of organic light emitting diodes on the substrate.
- 5 10. A method according to claim 8, wherein the organic material to be removed covers a bond pad region of the substrate.
- 10 11. A method according to claim 9 or 10, comprising removal of organic material from at least one organic light emitting diode pixel of the array of organic light emitting diode pixels.
12. A method according to any preceding claim, further comprising using the beam of ions to remove a layer of electrically conducting polymeric material in the defined areas.